Docket No. 8017-1169 Appln. No. 10/536,993



AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

- 1. (original) A semiconductor device comprising connection plug wherein a nanomaterial is substantially uniformly disposed in a section of the connection plug formed from a metal.
- 2. (original) A semiconductor device comprising an interconnection wherein a nanomaterial is substantially uniformly formed on a bottom surface of the interconnection formed from a metal.
- 3. (original) The semiconductor device according to claim 1, wherein the nanomaterial is a fibrous carbon nanomaterial, a particle-like carbon nanomaterial or a thin silicon wire.
- 4. (original) The semiconductor device according to claim 2, wherein the nanomaterial is a fibrous carbon nanomaterial, a granular particle-like carbon nanomaterial or a thin silicon wire.
- 5. (original) The semiconductor device according to claim 1, wherein the nanomaterial is oriented substantially perpendicularly to a substrate.
 - 6. (original) The semiconductor device according to claim 2, wherein the nanomaterial is oriented substantially perpendicularly to a substrate.

- 7. (original) The semiconductor device according to claim 1, wherein the nanomaterial is provided in the whole connection plug.
- 8. (original) The semiconductor device according to claim 2, wherein the nanomaterial is provided up to the vicinity of a top surface of the interconnection.
- 9. (original) The semiconductor device according to claim 1, wherein the metal is formed by an MOCVD method or a plating method.
- 10. (original) The semiconductor device according to claim 2, wherein the metal is formed by an MOCVD method or a plating method.

11-19. (canceled)

- 20. (original) The semiconductor device according to claim 1, wherein the connection plug formed from a metal is formed by a plating method which involves using a plating liquid containing a nanomaterial.
- 21. (original) The semiconductor device according to claim 2, wherein the interconnection formed from a metal is formed by a plating method which involves using a plating liquid containing a nanomaterial.

22-26. (canceled)